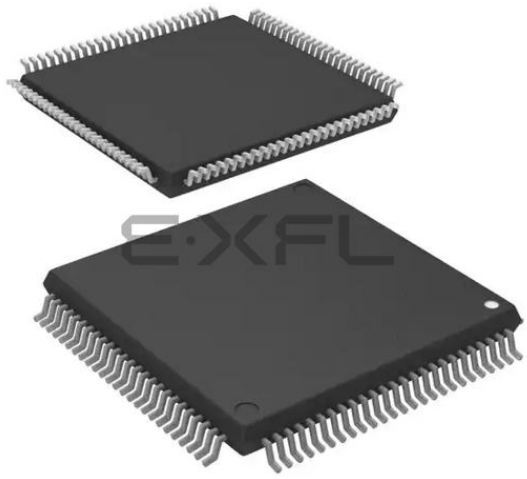
Renesas Electronics America Inc - R5F3650NCNFB#V0 Datasheet



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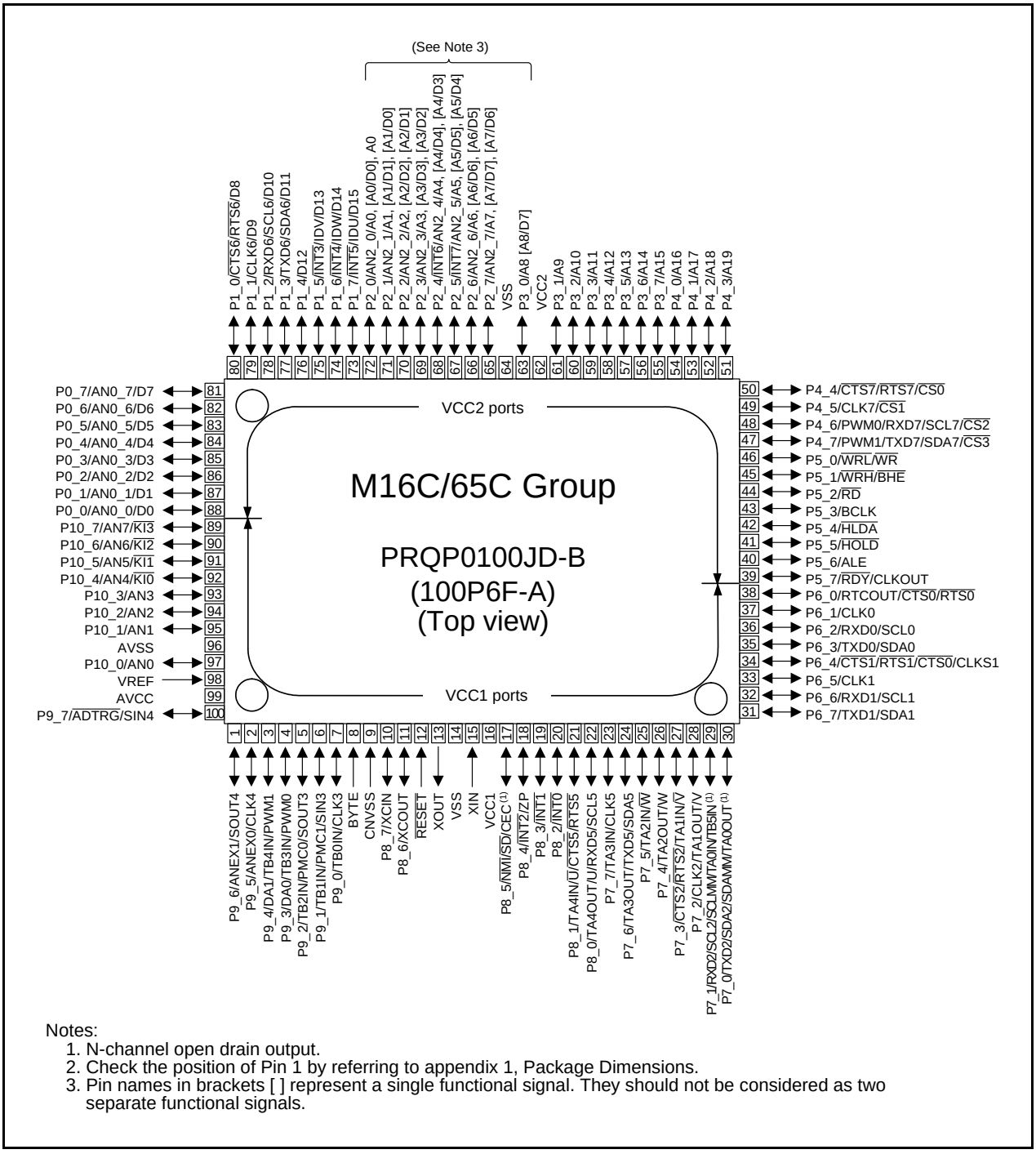
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	M16C/60
Core Size	16-Bit
Speed	32MHz
Connectivity	EBI/EMI, I²C, SIO, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	85
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	47K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 26x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LFQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f3650ncnfb-v0



Notes:
1. N-channel open drain output.
2. Check the position of Pin 1 by referring to appendix 1, Package Dimensions.
3. Pin names in brackets [ ] represent a single functional signal. They should not be considered as two separate functional signals.

Figure 1.6 Pin Assignment for the 100-Pin Package

Table 1.11 Pin Names for the 100-Pin Package (2/2)

Pin No.		Control Pin	Port	I/O Pin for Peripheral Function				Bus Control Pin
FA	FB			Interrupt	Timer	Serial interface	A/D converter, D/A converter	
51	49		P4_3					A19
52	50		P4_2					A18
53	51		P4_1					A17
54	52		P4_0					A16
55	53		P3_7					A15
56	54		P3_6					A14
57	55		P3_5					A13
58	56		P3_4					A12
59	57		P3_3					A11
60	58		P3_2					A10
61	59		P3_1					A9
62	60	VCC2						
63	61		P3_0					A8, [A8/D7]
64	62	VSS						
65	63		P2_7				AN2_7	A7, [A7/D7], [A7/D6]
66	64		P2_6				AN2_6	A6, [A6/D6], [A6/D5]
67	65		P2_5	$\overline{\text{INT7}}$			AN2_5	A5, [A5/D5], [A5/D4]
68	66		P2_4	$\overline{\text{INT6}}$			AN2_4	A4, [A4/D4], [A4/D3]
69	67		P2_3				AN2_3	A3, [A3/D3], [A3/D2]
70	68		P2_2				AN2_2	A2, [A2/D2], [A2/D1]
71	69		P2_1				AN2_1	A1, [A1/D1], [A1/D0]
72	70		P2_0				AN2_0	A0, [A0/D0], A0
73	71		P1_7	$\overline{\text{INT5}}$	IDU			D15
74	72		P1_6	$\overline{\text{INT4}}$	IDW			D14
75	73		P1_5	$\overline{\text{INT3}}$	IDV			D13
76	74		P1_4					D12
77	75		P1_3			TXD6/SDA6		D11
78	76		P1_2			RXD6/SCL6		D10
79	77		P1_1			CLK6		D9
80	78		P1_0			$\overline{\text{CTS6}}$/$\overline{\text{RTS6}}$		D8
81	79		P0_7				AN0_7	D7
82	80		P0_6				AN0_6	D6
83	81		P0_5				AN0_5	D5
84	82		P0_4				AN0_4	D4
85	83		P0_3				AN0_3	D3
86	84		P0_2				AN0_2	D2
87	85		P0_1				AN0_1	D1
88	86		P0_0				AN0_0	D0
89	87		P10_7	$\overline{\text{KI3}}$			AN7	
90	88		P10_6	$\overline{\text{KI2}}$			AN6	
91	89		P10_5	$\overline{\text{KI1}}$			AN5	
92	90		P10_4	$\overline{\text{KI0}}$			AN4	
93	91		P10_3				AN3	
94	92		P10_2				AN2	
95	93		P10_1				AN1	
96	94	AVSS						
97	95		P10_0				AN0	
98	96	VREF						
99	97	AVCC						
100	98		P9_7			SIN4	$\overline{\text{ADTRG}}$	

Table 1.13 Pin Functions for the 128-Pin Package (2/3)

Signal Name	Pin Name	I/O	Power Supply	Description
Main clock input	XIN	I	VCC1	I/O for the main clock oscillator. Connect a ceramic resonator or crystal between pins XIN and XOUT. (1) Input an external clock to XIN pin and leave XOUT pin open.
Main clock output	XOUT	O	VCC1	
Sub clock input	XCIN	I	VCC1	I/O for a sub clock oscillator. Connect a crystal between pins XCIN and XCOUT. (1) Input an external clock to XCIN pin and leave XCOUT pin open.
Sub clock output	XCOUT	O	VCC1	
BCLK output	BCLK	O	VCC2	Outputs the BCLK signal.
Clock output	CLKOUT	O	VCC2	Outputs a clock with the same frequency as fC, f1, f8, or f32.
$\overline{INT}$ interrupt input	$\overline{INT0}$ to $\overline{INT2}$	I	VCC1	Input for the $\overline{INT}$ interrupt.
	$\overline{INT3}$ to $\overline{INT7}$	I	VCC2	
$\overline{NMI}$ interrupt input	$\overline{NMI}$	I	VCC1	Input for the $\overline{NMI}$ interrupt.
Key input interrupt input	$\overline{KI0}$ to $\overline{KI3}$	I	VCC1	Input for the key input interrupt.
Timer A	TA0OUT to TA4OUT	I/O	VCC1	I/O for timers A0 to A4 (TA0OUT is N-channel open drain output).
	TA0IN to TA4IN	I	VCC1	Input for timers A0 to A4.
	ZP	I	VCC1	Input for Z-phase.
Timer B	TB0IN to TB5IN	I	VCC1	Input for timers B0 to B5.
Three-phase motor control timer	U, $\overline{U}$, V, $\overline{V}$, W, $\overline{W}$	O	VCC1	Output for the three-phase motor control timer.
	$\overline{SD}$	I	VCC1	Forced cutoff input.
	IDU, IDV, IDW	I	VCC2	Input for the position data.
Real-time clock output	RTCOUT	O	VCC1	Output for the real-time clock.
PWM output	PWM0, PWM1	O	VCC1, VCC2	PWM output.
Remote control signal receiver input	PMC0, PMC1	I	VCC1	Input for the remote control signal receiver.
Serial interface UART0 to UART2, UART5 to UART7	$\overline{CTS0}$ to $\overline{CTS2}$, $\overline{CTS5}$	I	VCC1	Input pins to control data transmission.
	$\overline{CTS6}$, $\overline{CTS7}$	I	VCC2	
	$\overline{RTS0}$ to $\overline{RTS2}$, $\overline{RTS5}$	O	VCC1	Output pins to control data reception.
	$\overline{RTS6}$, $\overline{RTS7}$	O	VCC2	
	CLK0 to CLK2, CLK5	I/O	VCC1	Transmit/receive clock I/O.
	CLK6, CLK7	I/O	VCC2	
	RXD0 to RXD2, RXD5	I	VCC1	Serial data input.
	RXD6, RXD7	I	VCC2	
	TXD0 to TXD2, TXD5	O	VCC1	Serial data output. (2)
	TXD6, TXD7	O	VCC2	
	CLKS1	O	VCC1	Output for the transmit/receive clock multiple-pin output function.

Notes:
1. Contact the manufacturer of crystal/ceramic resonator regarding the oscillation characteristics.
2. TXD2, SDA2, and SCL2 are N-channel open drain output pins. TXDi (i = 0, 1, 5 to 7), SDAi, and SCLi can be selected as CMOS output pins or N-channel open drain output pins.

Table 1.14 Pin Functions for the 128-Pin Package (3/3)

Signal Name	Pin Name	I/O	Power Supply	Description
UART0 to UART2, UART5 to UART7 I^2C mode	SDA0 to SDA2, SDA5	I/O	VCC1	Serial data I/O.
	SDA6, SDA7	I/O	VCC2	
	SCL0 to SCL2, SCL5	I/O	VCC1	Transmit/receive clock I/O.
	SCL6, SCL7	I/O	VCC2	
Serial interface SI/O3, SI/O4	CLK3, CLK4	I/O	VCC1	Transmit/receive clock I/O.
	SIN3, SIN4	I	VCC1	Serial data input.
	SOUT3, SOUT4	O	VCC1	Serial data output.
Multi-master I^2C-bus interface	SDAMM	I/O	VCC1	Serial data I/O (N-channel open drain output).
	SCLMM	I/O	VCC1	Transmit/receive clock I/O (N-channel open drain output).
CEC I/O	CEC	I/O	VCC1	CEC I/O (N-channel open drain output).
Reference voltage input	VREF	I	VCC1	Reference voltage input for the A/D and D/A converters.
A/D converter	AN0 to AN7	I	VCC1	Analog input.
	AN0_0 to AN0_7 AN2_0 to AN2_7	I	VCC2	
	$\overline{\text{ADTRG}}$	I	VCC1	External trigger input.
	ANEX0, ANEX1	I	VCC1	Extended analog input.
D/A converter	DA0, DA1	O	VCC1	Output pin the D/A converter.
I/O ports	P0_0 to P0_7 P1_0 to P1_7 P2_0 to P2_7 P3_0 to P3_7 P4_0 to P4_7 P5_0 to P5_7 P12_0 to P12_7 P13_0 to P13_7	I/O	VCC2	8-bit CMOS I/O ports. A direction register determines whether each pin is used as an input port or an output port. A pull-up resistor may be enabled or disabled for input ports in 4-bit units.
	P6_0 to P6_7 P7_0 to P7_7 P8_0 to P8_7 P9_0 to P9_7 P10_0 to P10_7 P11_0 to P11_7	I/O	VCC1	8-bit I/O ports having equivalent functions to P0. However, P7_0, P7_1, and P8_5 are N-channel open drain output ports. No pull-up resistor is provided. P8_5 is an input port for verifying the $\overline{\text{NMI}}$ pin level and shares a pin with $\overline{\text{NMI}}$.
	P14_0, P14_1	I/O	VCC1	I/O ports having equivalent functions to P0.

Table 1.15 Pin Functions for the 100-Pin Package (1/3)

Signal Name	Pin Name	I/O	Power Supply	Description
Power supply input	VCC1, VCC2, VSS	I	-	Apply 2.7 to 5.5 V to pins VCC1 and VCC2 (VCC1 ≥ VCC2) and 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	VCC1	This is the power supply for the A/D and D/A converters. Connect the AVCC pin to VCC1, and connect the AVSS pin to VSS.
Reset input	$\overline{\text{RESET}}$	I	VCC1	Driving this pin low resets the MCU.
CNVSS	CNVSS	I	VCC1	Input pin to switch processor modes. After a reset, to start operating in single-chip mode, connect the CNVSS pin to VSS via a resistor. To start operating in microprocessor mode, connect the pin to VCC1.
External data bus width select input	BYTE	I	VCC1	Input pin to select the data bus of the external area. The data bus is 16 bits when it is low, and 8 bits when it is high. This pin must be fixed either high or low. Connect the BYTE pin to VSS in single-chip mode.
Bus control pins	D0 to D7	I/O	VCC2	Inputs or outputs data (D0 to D7) while accessing an external area with a separate bus.
	D8 to D15	I/O	VCC2	Inputs or outputs data (D8 to D15) while accessing an external area with a 16-bit separate bus.
	A0 to A19	O	VCC2	Outputs address bits A0 to A19.
	A0/D0 to A7/D7	I/O	VCC2	Inputs or outputs data (D0 to D7) and outputs address bits (A0 to A7) by timesharing, while accessing an external area with an 8-bit multiplexed bus.
	A1/D0 to A8/D7	I/O	VCC2	Inputs or outputs data (D0 to D7) and outputs address bits (A1 to A8) by timesharing, while accessing an external area with a 16-bit multiplexed bus.
	$\overline{\text{CS0}}$ to $\overline{\text{CS3}}$	O	VCC2	Outputs chip-select signals $\overline{\text{CS0}}$ to $\overline{\text{CS3}}$ to specify an external area.
	$\overline{\text{WRL}}$/$\overline{\text{WR}}$ $\overline{\text{WRH}}$/$\overline{\text{BHE}}$ $\overline{\text{RD}}$	O	VCC2	Outputs $\overline{\text{WRL}}$, $\overline{\text{WRH}}$, ($\overline{\text{WR}}$, $\overline{\text{BHE}}$), and $\overline{\text{RD}}$ signals. $\overline{\text{WRL}}$ and $\overline{\text{WRH}}$ can be switched with $\overline{\text{BHE}}$ and $\overline{\text{WR}}$. • $\overline{\text{WRL}}$, $\overline{\text{WRH}}$, and $\overline{\text{RD}}$ selected If the external data bus is 16 bits, data is written to an even address in an external area when $\overline{\text{WRL}}$ is driven low. Data is written to an odd address when $\overline{\text{WRH}}$ is driven low. Data is read when $\overline{\text{RD}}$ is driven low. • $\overline{\text{WR}}$, $\overline{\text{BHE}}$, and $\overline{\text{RD}}$ selected Data is written to an external area when $\overline{\text{WR}}$ is driven low. Data in an external area is read when $\overline{\text{RD}}$ is driven low. An odd address is accessed when $\overline{\text{BHE}}$ is driven low. Select $\overline{\text{WR}}$, $\overline{\text{BHE}}$, and $\overline{\text{RD}}$ when using an 8-bit external data bus.
	ALE	O	VCC2	Outputs an ALE signal to latch the address.
	$\overline{\text{HOLD}}$	I	VCC2	$\overline{\text{HOLD}}$ input is unavailable. Connect the $\overline{\text{HOLD}}$ pin to VCC2 via a resistor (pull-up).
	$\overline{\text{HLDA}}$	O	VCC2	In a hold state, $\overline{\text{HLDA}}$ outputs a low-level signal.
	$\overline{\text{RDY}}$	I	VCC2	The MCU bus is placed in a wait state while the $\overline{\text{RDY}}$ pin is driven low.

Power supply: VCC2 is used to supply power to the external bus associated pins. The dual power supply configuration allows VCC2 to interface at a different voltage than VCC1.

2.1 Data Registers (R0, R1, R2, and R3)

R0, R1, R2, and R3 are 16-bit registers used for transfer, arithmetic, and logic operations. R0 and R1 can be split into upper (R0H/R1H) and lower (R0L/R1L) bits to be used separately as 8-bit data registers. R0 can be combined with R2, and R3 can be combined with R1 and be used as 32-bit data registers R2R0 and R3R1, respectively.

2.2 Address Registers (A0 and A1)

A0 and A1 are 16-bit registers used for indirect addressing, relative addressing, transfer, arithmetic, and logic operations. A0 can be combined with A1 and used as a 32-bit address register (A1A0).

2.3 Frame Base Register (FB)

FB is a 16-bit register that is used for FB relative addressing.

2.4 Interrupt Table Register (INTB)

INTB is a 20-bit register that indicates the start address of a relocatable interrupt vector table.

2.5 Program Counter (PC)

The PC is 20 bits wide and indicates the address of the next instruction to be executed.

2.6 User Stack Pointer (USP) and Interrupt Stack Pointer (ISP)

The USP and ISP stack pointers (SP) are each comprised of 16 bits. The U flag is used to switch between USP and ISP.

2.7 Static Base Register (SB)

SB is a 16-bit register used for SB relative addressing.

2.8 Flag Register (FLG)

FLG is an 11-bit register that indicates the CPU state.

2.8.1 Carry Flag (C Flag)

The C flag retains a carry, borrow, or shift-out bit generated by the arithmetic/logic unit.

2.8.2 Debug Flag (D Flag)

The D flag is for debugging only. Set it to 0.

2.8.3 Zero Flag (Z Flag)

The Z flag becomes 1 when an arithmetic operation results in 0. Otherwise, it becomes 0.

2.8.4 Sign Flag (S Flag)

The S flag becomes 1 when an arithmetic operation results in a negative value. Otherwise, it becomes 0.

2.8.5 Register Bank Select Flag (B Flag)

Register bank 0 is selected when the B flag is 0. Register bank 1 is selected when this flag is 1.

2.8.6 Overflow Flag (O Flag)

The O flag becomes 1 when an arithmetic operation results in an overflow. Otherwise, it becomes 0.

Table 4.5 SFR Information (5) (1)

Address	Register	Symbol	Reset Value
0180h	DMA0 Source Pointer	SAR0	XXh
0181h			XXh
0182h			0Xh
0183h			
0184h	DMA0 Destination Pointer	DAR0	XXh
0185h			XXh
0186h			0Xh
0187h			
0188h	DMA0 Transfer Counter	TCR0	XXh
0189h			XXh
018Ah			
018Bh			
018Ch	DMA0 Control Register	DM0CON	0000 0X00b
018Dh			
018Eh			
018Fh			
0190h	DMA1 Source Pointer	SAR1	XXh
0191h			XXh
0192h			0Xh
0193h			
0194h	DMA1 Destination Pointer	DAR1	XXh
0195h			XXh
0196h			0Xh
0197h			
0198h	DMA1 Transfer Counter	TCR1	XXh
0199h			XXh
019Ah			
019Bh			
019Ch	DMA1 Control Register	DM1CON	0000 0X00b
019Dh			
019Eh			
019Fh			
01A0h	DMA2 Source Pointer	SAR2	XXh
01A1h			XXh
01A2h			0Xh
01A3h			
01A4h	DMA2 Destination Pointer	DAR2	XXh
01A5h			XXh
01A6h			0Xh
01A7h			
01A8h	DMA2 Transfer Counter	TCR2	XXh
01A9h			XXh
01AAh			
01ABh			
01ACh	DMA2 Control Register	DM2CON	0000 0X00b
01ADh			
01AEh			
01AFh			

X: Undefined

Note:
1. The blank areas are reserved. No access is allowed.

Table 4.10 SFR Information (10) (1)

Address	Register	Symbol	Reset Value
0270h	SI/O3 Transmit/Receive Register	S3TRR	XXh
0271h			
0272h	SI/O3 Control Register	S3C	0100 0000b
0273h	SI/O3 Bit Rate Register	S3BRG	XXh
0274h	SI/O4 Transmit/Receive Register	S4TRR	XXh
0275h			
0276h	SI/O4 Control Register	S4C	0100 0000b
0277h	SI/O4 Bit Rate Register	S4BRG	XXh
0278h	SI/O3, 4 Control Register 2	S34C2	00XX X0X0b
0279h			
027Ah			
027Bh			
027Ch			
027Dh			
027Eh			
027Fh			
0280h			
0281h			
0282h			
0283h			
0284h	UART5 Special Mode Register 4	U5SMR4	00h
0285h	UART5 Special Mode Register 3	U5SMR3	000X 0X0Xb
0286h	UART5 Special Mode Register 2	U5SMR2	X000 0000b
0287h	UART5 Special Mode Register	U5SMR	X000 0000b
0288h	UART5 Transmit/Receive Mode Register	U5MR	00h
0289h	UART5 Bit Rate Register	U5BRG	XXh
028Ah	UART5 Transmit Buffer Register	U5TB	XXh
028Bh			XXh
028Ch	UART5 Transmit/Receive Control Register 0	U5C0	0000 1000b
028Dh	UART5 Transmit/Receive Control Register 1	U5C1	0000 0010b
028Eh	UART5 Receive Buffer Register	U5RB	XXh
028Fh			XXh
0290h			
0291h			
0292h			
0293h			
0294h	UART6 Special Mode Register 4	U6SMR4	00h
0295h	UART6 Special Mode Register 3	U6SMR3	000X 0X0Xb
0296h	UART6 Special Mode Register 2	U6SMR2	X000 0000b
0297h	UART6 Special Mode Register	U6SMR	X000 0000b
0298h	UART6 Transmit/Receive Mode Register	U6MR	00h
0299h	UART6 Bit Rate Register	U6BRG	XXh
029Ah	UART6 Transmit Buffer Register	U6TB	XXh
029Bh			XXh
029Ch	UART6 Transmit/Receive Control Register 0	U6C0	0000 1000b
029Dh	UART6 Transmit/Receive Control Register 1	U6C1	0000 0010b
029Eh	UART6 Receive Buffer Register	U6RB	XXh
029Fh			XXh

X: Undefined

Note:
1. The blank areas are reserved. No access is allowed.

4.2 Notes on SFRs

4.2.1 Register Settings

Table 4.19 lists Registers with Write-Only Bits and registers whose function differs between reading and writing. Set these registers with immediate values. Do not use read-modify-write instructions. When establishing the next value by altering the existing value, write the existing value to the RAM as well as to the register. Transfer the next value to the register after making changes in the RAM.
Read-modify-write instructions can be used when writing to the no register bits.

Table 4.19 Registers with Write-Only Bits

Address	Register	Symbol
0249h	UART0 Bit Rate Register	U0BRG
024Bh to 024Ah	UART0 Transmit Buffer Register	U0TB
0259h	UART1 Bit Rate Register	U1BRG
025Bh to 025Ah	UART1 Transmit Buffer Register	U1TB
0269h	UART2 Bit Rate Register	U2BRG
026Bh to 026Ah	UART2 Transmit Buffer Register	U2TB
0273h	SI/O3 Bit Rate Register	S3BRG
0277h	SI/O4 Bit Rate Register	S4BRG
0289h	UART5 Bit Rate Register	U5BRG
028Bh to 028Ah	UART5 Transmit Buffer Register	U5TB
0299h	UART6 Bit Rate Register	U6BRG
029Bh to 029Ah	UART6 Transmit Buffer Register	U6TB
02A9h	UART7 Bit Rate Register	U7BRG
02ABh to 02AAh	UART7 Transmit Buffer Register	U7TB
02B6h	I2C0 Control Register 1	S3D0
02B8h	I2C0 Status Register 0	S10
0303h to 0302h	Timer A1-1 Register	TA11
0305h to 0304h	Timer A2-1 Register	TA21
0307h to 0306h	Timer A4-1 Register	TA41
030Ah	Three-Phase Output Buffer Register 0	IDB0
030Bh	Three-Phase Output Buffer Register 1	IDB1
030Ch	Dead Time Timer	DTT
030Dh	Timer B2 Interrupt Generation Frequency Set Counter	ICTB2
0327h to 0326h	Timer A0 Register	TA0
0329h to 0328h	Timer A1 Register	TA1
032Bh to 032Ah	Timer A2 Register	TA2
032Dh to 032Ch	Timer A3 Register	TA3
032Fh to 032Eh	Timer A4 Register	TA4
037Dh	Watchdog Timer Refresh Register	WDTR
037Eh	Watchdog Timer Start Register	WDTS

Table 5.10 Flash Memory (Data Flash) Electrical Characteristics

V_{CC1} = 2.7 to 5.5 V at T_{opr} = -20 to 85°C/-40 to 85°C, unless otherwise specified.

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
-	Program and erase cycles (1), (3), (4)	V_{CC1} = 3.3 V, T_{opr} = 25°C	10,000 (2)			times
-	2 word program time	V_{CC1} = 3.3 V, T_{opr} = 25°C		300	4000	µs
-	Lock bit program time	V_{CC1} = 3.3 V, T_{opr} = 25°C		140	3000	µs
-	Block erase time	V_{CC1} = 3.3 V, T_{opr} = 25°C		0.2	3.0	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend				$5 + \frac{3}{f_{(BCLK)}}$	ms
-	Interval from erase start/restart until following suspend request		0			µs
-	Suspend interval necessary for auto-erasure to complete (7)		20			ms
-	Time from suspend until erase restart				$30 + \frac{1}{f_{(BCLK)}}$	µs
-	Program, erase voltage		2.7		5.5	V
-	Read voltage		2.7		5.5	V
-	Program, erase temperature		–20/–40		85	°C
t_{PS}	Flash memory circuit stabilization wait time				50	µs
-	Data hold time (6)	Ambient temperature = 55°C	20			year

Notes:
1. Definition of program and erase cycles
   The program and erase cycles refer to the number of per-block erasures.
   If the program and erase cycles are n (n = 10,000), each block can be erased n times.
   For example, if a 4 KB block is erased after writing 2 word data 1,024 times, each to a different address, this counts as one program and erase cycles. Data cannot be written to the same address more than once without erasing the block (rewrite prohibited).
2. Cycles to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 256 groups before erasing them all in one operation. In addition, averaging the erasure cycles between blocks A and B can further reduce the actual erasure cycles. It is also advisable to retain data on the erasure cycles of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact a Renesas Electronics sales office.
6. The data hold time includes time that the power supply is off or the clock is not supplied.
7. After an erase start or erase restart, if an interval of at least 20 ms is not set before the next suspend request, the erase sequence cannot be completed.

Table 5.15 Power Supply Circuit Timing Characteristics

The measurement condition is V_{CC1} = 2.7 to 5.5 V and T_{opr} = 25°C, unless otherwise specified.

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Internal power supply stability time when power is on (1)				5	ms
$t_{d(R-S)}$	STOP release time				150	µs
$t_{d(W-S)}$	Low power mode wait mode release time				150	µs

Note:
1. Waiting time until the internal power supply generator stabilizes when power is on.

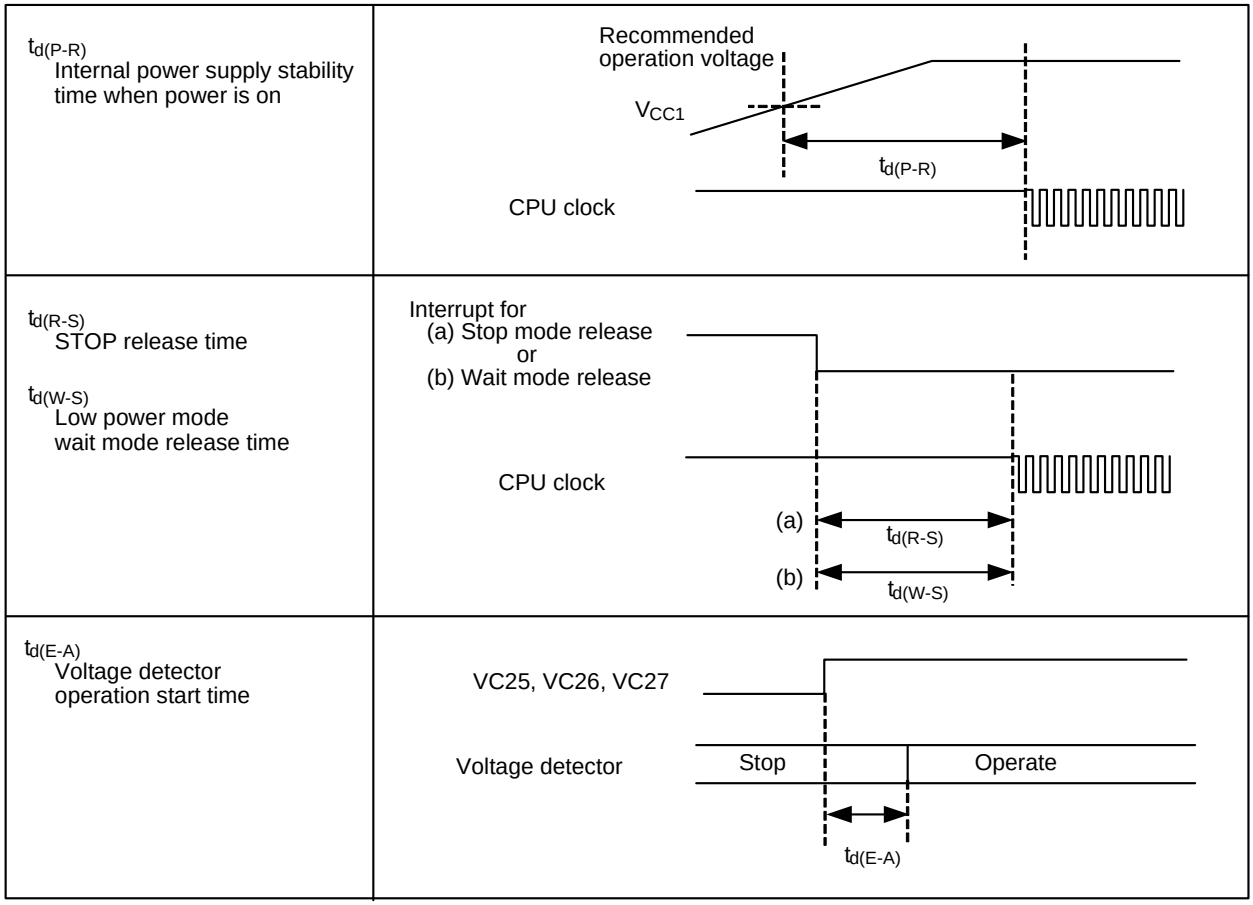


Figure 5.4 Power Supply Circuit Timing Diagram

$V_{CC1} = V_{CC2} = 5\ V$

5.2.2 Timing Requirements (Peripheral Functions and Others)

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.2.2.1 Reset Input ($\overline{\text{RESET}}$ Input)

Table 5.22 Reset Input ($\overline{\text{RESET}}$ Input)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(RSTL)}$	$\overline{\text{RESET}}$ input low pulse width	10		µs

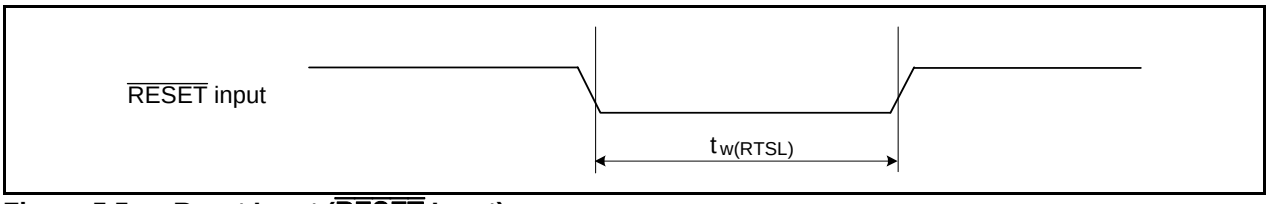


Figure 5.5 Reset Input ($\overline{\text{RESET}}$ Input)

5.2.2.2 External Clock Input

Table 5.23 External Clock Input (XIN Input) (1)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
t_c	External clock input cycle time	50		ns
$t_{w(H)}$	External clock input high pulse width	20		ns
$t_{w(L)}$	External clock input low pulse width	20		ns
t_r	External clock rise time		9	ns
t_f	External clock fall time		9	ns

Note:
1. The condition is $V_{CC1} = V_{CC2} = 3.0$ to 5.0 V.

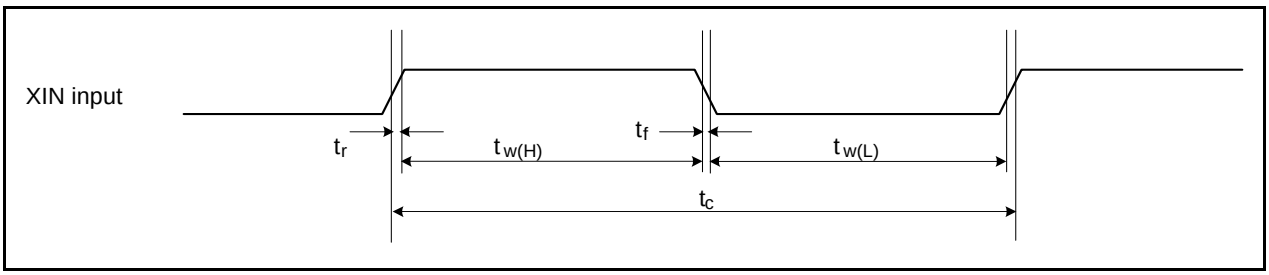


Figure 5.6 External Clock Input (XIN Input)

$V_{CC1} = V_{CC2} = 5\ V$

Timing Requirements

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at $T_{opr} = -20°C$ to 85°C/-40°C to 85°C unless otherwise specified)

5.2.2.3 Timer A Input

Table 5.24 Timer A Input (Counter Input in Event Counter Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	100		ns
$t_{w(TAH)}$	TAiIN input high pulse width	40		ns
$t_{w(TAL)}$	TAiIN input low pulse width	40		ns

Table 5.25 Timer A Input (Gating Input in Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	400		ns
$t_{w(TAH)}$	TAiIN input high pulse width	200		ns
$t_{w(TAL)}$	TAiIN input low pulse width	200		ns

Table 5.26 Timer A Input (External Trigger Input in One-Shot Timer Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TA)}$	TAiIN input cycle time	200		ns
$t_{w(TAH)}$	TAiIN input high pulse width	100		ns
$t_{w(TAL)}$	TAiIN input low pulse width	100		ns

Table 5.27 Timer A Input (External Trigger Input in Pulse Width Modulation Mode and Programmable Output Mode)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{w(TAH)}$	TAiIN input high pulse width	100		ns
$t_{w(TAL)}$	TAiIN input low pulse width	100		ns

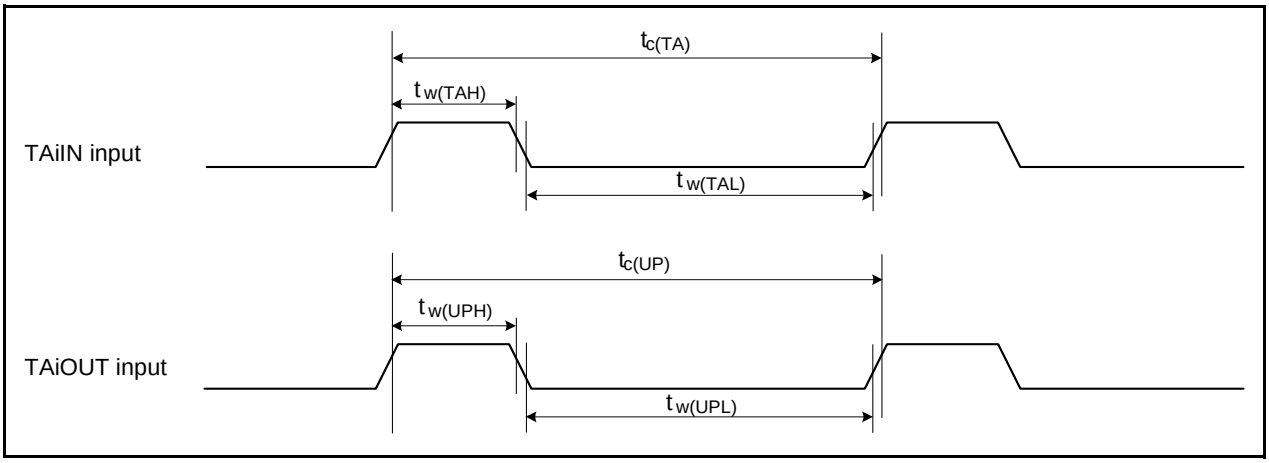


Figure 5.7 Timer A Input

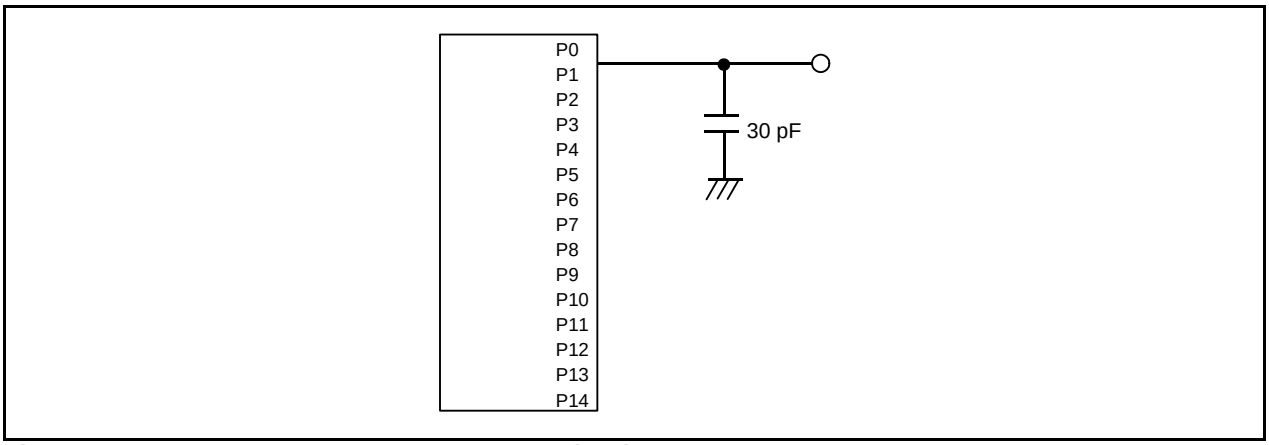


Figure 5.14 Ports P0 to P14 Measurement Circuit

$V_{CC1} = V_{CC2} = 5$ V

Switching Characteristics

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.2.4.2 In 1 to 3 Waits Setting and When Accessing External Area

Table 5.37 Memory Expansion Mode and Microprocessor Mode (in 1 to 3 Waits Setting and When Accessing External Area)

Symbol	Parameter	Measuring Condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	See Figure 5.14		25	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		0		ns
$t_{h(RD-AD)}$	Address output hold time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address output hold time (in relation to WR)		(Note 2)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			25	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		0		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time			15	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time		-4		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			25	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			25	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (in relation to BCLK)			40	ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(Note 1)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR)(3)		(Note 4)		ns

Notes:

1. Calculated according to the BCLK frequency as follows:

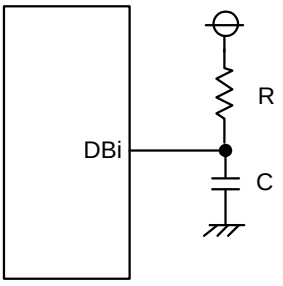
$$\frac{(n-0.5)\times 10^9}{f_{(BCLK)}} - 40[ns]$$

n is 1 for 1 wait setting, 2 for 2 waits setting and 3 for 3 waits setting.
When n = 1, $f_{(BCLK)}$ is 12.5 MHz or less.

2. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times 10^9}{f_{(BCLK)}} - 10[ns]$$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = -CR \times \ln(1 - V_{OL}/V_{CC2})$
by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC2}$, C = 30 pF, R = 1 kΩ, hold time of output low level is
$t = -30\text{ pF} \times 1\text{ k}\Omega \times \ln(1 - 0.2V_{CC2}/V_{CC2})$
= 6.7 ns.



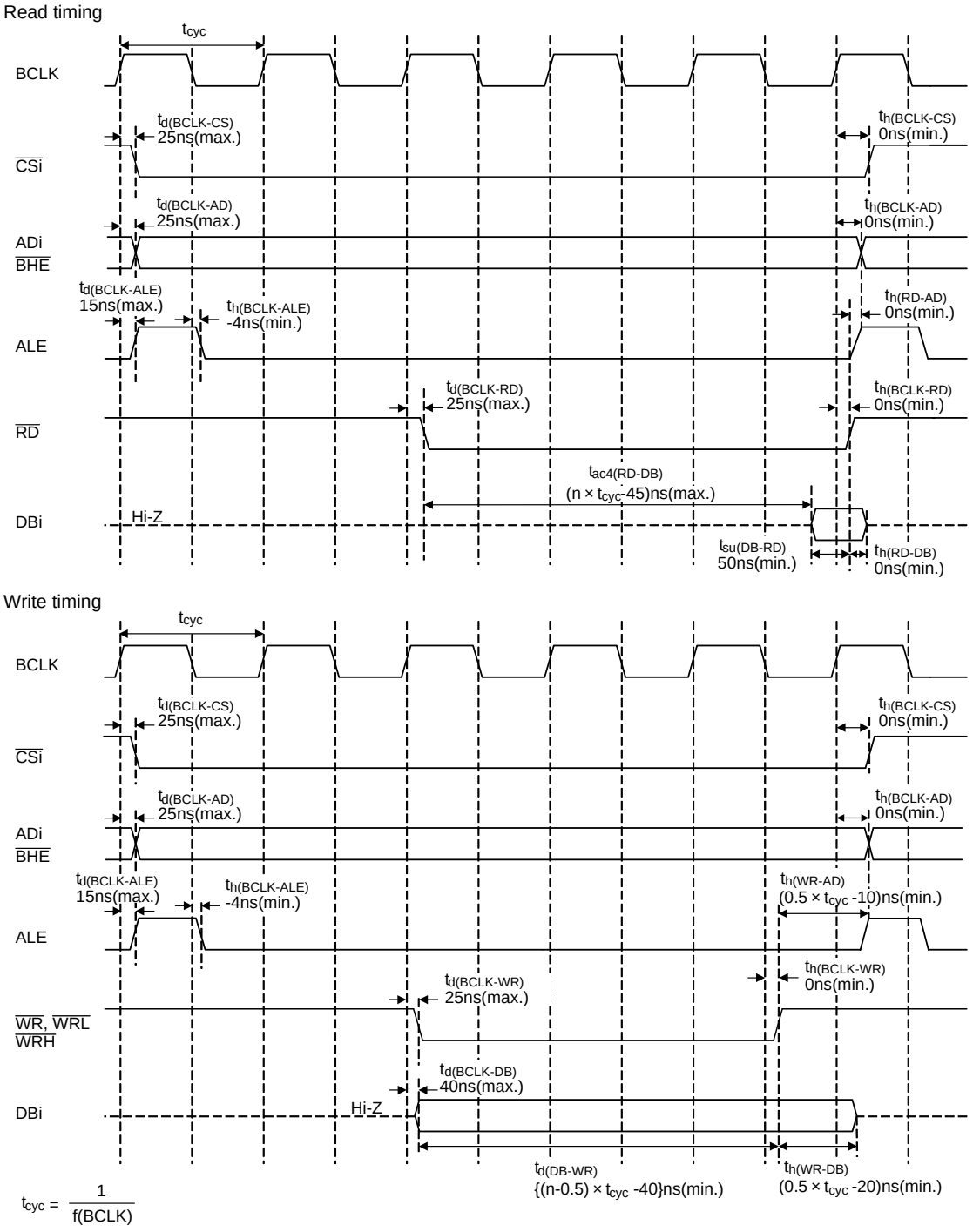
4. Calculated according to the BCLK frequency as follows:

$$\frac{0.5\times 10^9}{f_{(BCLK)}} - 20[ns]$$

Hold time is equal to or less than 0 ns when the BCLK frequency exceeds 25 MHz.

Memory Expansion Mode and Microprocessor Mode
(in wait state setting 2 ϕ + 3 ϕ, 2 ϕ + 4 ϕ, 3ϕ + 4 ϕ, and 4 ϕ + 5 ϕ, and when accessing external area)

$V_{CC1} = V_{CC2} = 5V$



$$t_{cyc} = \frac{1}{f(BCLK)}$$

Measuring conditions

- $V_{CC1} = V_{CC2} = 5V$
- Input timing voltage: V_{IL} = 0.8 V, V_{IH} = 2.0 V
- Output timing voltage: V_{OL} = 0.4 V, V_{OH} = 2.4 V

n: 3 (when 2 ϕ + 3 ϕ)
4 (when 2 ϕ + 4 ϕ or 3 ϕ + 4 ϕ)
5 (when 4 ϕ + 5 ϕ)

Figure 5.18 Timing Diagram

$V_{CC1} = V_{CC2} = 5\ V$

Switching Characteristics

($V_{CC1} = V_{CC2} = 5$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.2.4.5 In Wait State Setting 2φ + 3φ, 2φ + 4φ, 3φ + 4φ, and 4φ + 5φ, and When Inserting 1 to 3 Recovery Cycles and Accessing External Area

Table 5.40 Memory Expansion and Microprocessor Modes (in Wait State Setting 2φ + 3φ, 2φ + 4φ, 3φ + 4φ, and 4φ + 5φ, and When Inserting 1 to 3 Recovery Cycles and Accessing External Area)

Symbol	Parameter	Measuring Condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	See Figure 5.14		25	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		0		ns
$t_{h(RD-AD)}$	Address output hold time (in relation to RD)		(Note 4)		ns
$t_{h(WR-AD)}$	Address output hold time (in relation to WR)		(Note 2)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			25	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		0		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time			15	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time		-4		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			25	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			25	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (in relation to BCLK)			40	ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(Note 1)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR) (3)		(Note 5)		ns

Notes:

1. Calculated according to the BCLK frequency as follows:

$$\frac{n \times 10^9}{f_{(BCLK)}} - 40[ns]$$

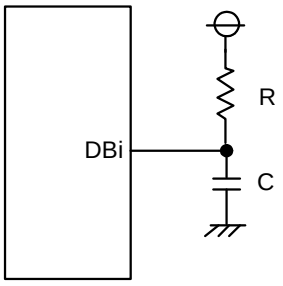
n is 3 for 2φ + 3φ, 4 for 2φ + 4φ, 4 for 3φ + 4φ, and 5 for 4φ + 5φ.

2. Calculated according to the BCLK frequency as follows:

$$\frac{m \times 10^9}{f_{(BCLK)}} - 10[ns]$$

m is 1 when 1 recovery cycle is inserted, 2 when 2 recovery cycles are inserted, and 3 when 3 recovery cycles are inserted.

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
Hold time of data bus is expressed in
$t = -CR \times \ln(1 - V_{OL}/V_{CC2})$
by a circuit of the right figure.
For example, when $V_{OL} = 0.2V_{CC2}$, C = 30 pF, R = 1 kΩ, hold time of output low level is
$t = -30\ pF \times 1\ k\Omega \times \ln(1 - 0.2V_{CC2}/V_{CC2})$
= 6.7 ns.



4. Calculated according to the BCLK frequency as follows:

$$\frac{m \times 10^9}{f_{(BCLK)}} + 0[ns]$$

m is 1 when 1 recovery cycle is inserted, 2 when 2 recovery cycles are inserted, and 3 when 3 recovery cycles are inserted.

5. Calculated according to the BCLK frequency as follows:

$$\frac{m \times 10^9}{f_{(BCLK)}} - 20[ns]$$

m is 1 when 1 recovery cycle is inserted, 2 when 2 recovery cycles are inserted, and 3 when 3 recovery cycles are inserted.

5.3 Electrical Characteristics (V_{CC1} = V_{CC2} = 3 V)

5.3.1 Electrical Characteristics

VCC1 = VCC2 = 3 V

Table 5.41 Electrical Characteristics (1) [1]

V_{CC1} = V_{CC2} = 2.7 to 3.3 V, V_{SS} = 0 V at T_{opr} = -20°C to 85°C/-40°C to 85°C, $f_{(BCLK)}$ = 32 MHz unless otherwise specified.

Symbol	Parameter			Measuring Condition	Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	High output voltage	P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1		I_{OH} = –1 mA	V_{CC1} – 0.5		V_{CC1}	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		I_{OH} = –1 mA	V_{CC2} – 0.5		V_{CC2}	
V_{OH}	High output voltage XOUT		HIGH POWER	I_{OH} = –0.1 mA	V_{CC1} – 0.5		V_{CC1}	V
			LOW POWER	I_{OH} = –50 µA	V_{CC1} – 0.5		V_{CC1}	
	High output voltage XCOUT		HIGH POWER	With no load applied		2.6		V
			LOW POWER	With no load applied		2.2		
V_{OL}	Low output voltage	P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P14_0, P14_1		I_{OL} = 1 mA			0.5	V
		P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P12_0 to P12_7, P13_0 to P13_7		I_{OL} = 1 mA			0.5	
		CEC		I_{OL} = 1 mA		0	0.5	V
V_{OL}	Low output voltage XOUT		HIGH POWER	I_{OL} = 0.1 mA			0.5	V
			LOW POWER	I_{OL} = 50 µA			0.5	
	Low output voltage XCOUT		HIGH POWER	With no load applied		0		V
			LOW POWER	With no load applied		0		
V_{T+}-V_{T-}	Hysteresis	$\overline{HOLD}$, $\overline{RDY}$, TA0IN to TA4IN, TB0IN to TB5IN, $\overline{INT0}$ to $\overline{INT7}$, $\overline{NMI}$, $\overline{ADTRG}$, $\overline{CTS0}$ to $\overline{CTS2}$, $\overline{CTS5}$ to $\overline{CTS7}$, SCL0 to SCL2, SCL5 to SCL7, SDA0 to SDA2, SDA5 to SDA7, CLK0 to CLK7, TA0OUT to TA4OUT, $\overline{KI0}$ to $\overline{KI3}$, RXD0 to RXD2, RXD5 to RXD7, SIN3, SIN4, $\overline{SD}$, PMC0, PMC1, SCLMM, SDAMM, ZP, IDU, IDV, IDW			0.2		1.0	V
		CEC			0.2	0.5	1.0	V
		$\overline{RESET}$			0.2		1.8	V
I_{IH}	High input current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1 XIN, $\overline{RESET}$, CNVSS, BYTE		V_I = 3 V			4.0	µA
–	Leakage current in powered-off state		CEC	V_{CC1} = 0 V			1.8	µA
I_{IL}	Low input current	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1 XIN, $\overline{RESET}$, CNVSS, BYTE		V_I = 0 V			–4.0	µA
R_{PULLUP}	Pull-up resistance	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_0 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_2 to P7_7, P8_0 to P8_4, P8_6, P8_7, P9_0 to P9_7, P10_0 to P10_7, P11_0 to P11_7, P12_0 to P12_7, P13_0 to P13_7, P14_0, P14_1		V_I = 0 V	50	80	150	kΩ
R_{fXIN}	Feedback resistance XIN					3.0		MΩ
V_{RAM}	RAM retention voltage			In stop mode	1.8			V

Note:
1. When $V_{CC1} \neq V_{CC2}$, refer to 5 V or 3 V standard depending on the voltage.

$V_{CC1} = V_{CC2} = 3\ V$

Table 5.44 Electrical Characteristics (3) (2/2)

R5F3651ECNFC, R5F3651KCNFC, R5F3650KCNFA, R5F3650KCNFB, R5F3651MCNFC, R5F3650MCNFA, R5F3650MCNFB, R5F3651NCNFC, R5F3650NCNFA, R5F3650NCNFB, R5F3651ECDFC, R5F3651KCDFC, R5F3650KCDFA, R5F3650KCDFB, R5F3651MCDFC, R5F3650MCDFA, R5F3650MCDFB, R5F3651NCDFC, R5F3650NCDFA, R5F3650NCDFB

$V_{CC1} = V_{CC2} = 2.7$ to $3.3\ V$, $V_{SS} = 0\ V$ at $T_{opr} = -20°C$ to $85°C/-40°C$ to $85°C$, $f_{(BCLK)} = 32$ MHz unless otherwise specified.

Symbol	Parameter	Measuring Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current In single-chip, mode, the output pin are open and other pins are V_{SS}	Stop mode	Main clock stopped 40 MHz on-chip oscillator stopped 125 kHz on-chip oscillator stopped Peripheral clock stopped $T_{opr} = 25°C$		1.6		µA
		During flash memory program	$f_{(BCLK)} = 10$ MHz, PM17 = 1 (one wait) $V_{CC1} = 3.0\ V$		20.0		mA
		During flash memory erase	$f_{(BCLK)} = 10$ MHz, PM17 = 1 (one wait) $V_{CC1} = 3.0\ V$		30.0		mA

$V_{CC1} = V_{CC2} = 3\ V$

5.3.4 Switching Characteristics (Memory Expansion Mode and Microprocessor Mode)

($V_{CC1} = V_{CC2} = 3$ V, $V_{SS} = 0$ V, at T_{opr} = -20°C to 85°C/-40°C to 85°C unless otherwise specified)

5.3.4.1 In No Wait State Setting

Table 5.59 Memory Expansion and Microprocessor Modes (in No Wait State Setting)

Symbol	Parameter	Measuring Condition	Standard		Unit
			Min.	Max.	
$t_{d(BCLK-AD)}$	Address output delay time	See Figure 5.29		30	ns
$t_{h(BCLK-AD)}$	Address output hold time (in relation to BCLK)		0		ns
$t_{h(RD-AD)}$	Address output hold time (in relation to RD)		0		ns
$t_{h(WR-AD)}$	Address output hold time (in relation to WR)		(Note 2)		ns
$t_{d(BCLK-CS)}$	Chip select output delay time			30	ns
$t_{h(BCLK-CS)}$	Chip select output hold time (in relation to BCLK)		0		ns
$t_{d(BCLK-ALE)}$	ALE signal output delay time			25	ns
$t_{h(BCLK-ALE)}$	ALE signal output hold time		–4		ns
$t_{d(BCLK-RD)}$	RD signal output delay time			30	ns
$t_{h(BCLK-RD)}$	RD signal output hold time		0		ns
$t_{d(BCLK-WR)}$	WR signal output delay time			30	ns
$t_{h(BCLK-WR)}$	WR signal output hold time		0		ns
$t_{d(BCLK-DB)}$	Data output delay time (in relation to BCLK)			40	ns
$t_{d(DB-WR)}$	Data output delay time (in relation to WR)		(Note 1)		ns
$t_{h(WR-DB)}$	Data output hold time (in relation to WR) (3)		(Note 4)		ns

Notes:

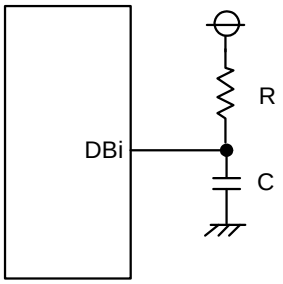
1. Calculated according to the BCLK frequency as follows:

   $\frac{0.5 \times 10^9}{f_{(BCLK)}} - 40[ns]$ $f_{(BCLK)}$ is 12.5 MHz or less.

2. Calculated according to the BCLK frequency as follows:

   $\frac{0.5 \times 10^9}{f_{(BCLK)}} - 15[ns]$

3. This standard value shows the timing when the output is off, and does not show hold time of data bus.
   Hold time of data bus varies with capacitor volume and pull-up (pull-down) resistance value.
   Hold time of data bus is expressed in
   $t = -CR \times \ln(1 - V_{OL}/V_{CC2})$
   by a circuit of the right figure.
   For example, when $V_{OL} = 0.2V_{CC2}$, C = 30 pF, R = 1 kΩ,
   hold time of output low level is
   $t = -30\ pF \times 1\ k\Omega \times \ln(1 - 0.2V_{CC2}/V_{CC2})$
   = 6.7 ns.



4. Calculated according to the BCLK frequency as follows:

   $\frac{0.5 \times 10^9}{f_{(BCLK)}} - 25[ns]$
   Hold time is equal to or less than 0 ns when the BCLK frequency exceeds 20 MHz.